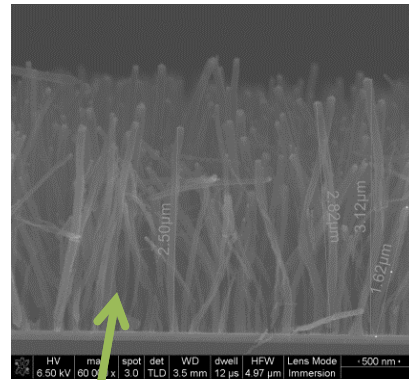
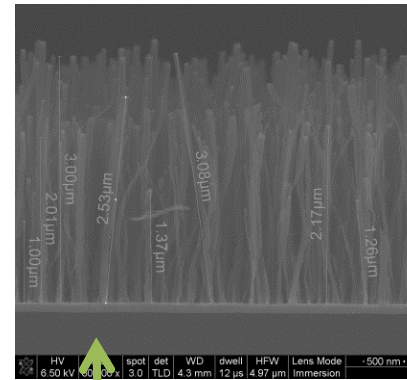


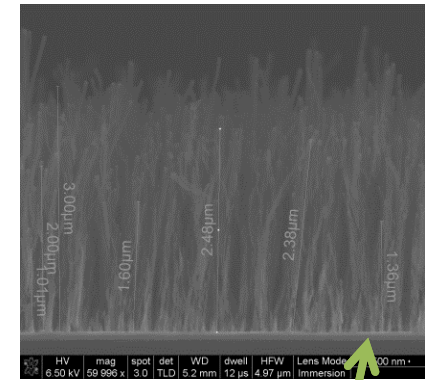
Length of CNTs on one wafer:
measured in 6 points, from the center to the edge of the wafer



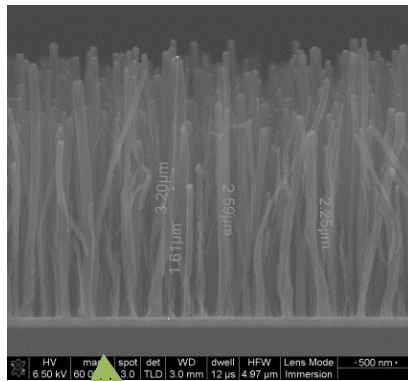
10 mm from center



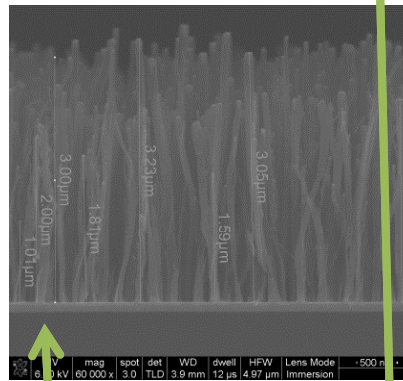
30 mm from center



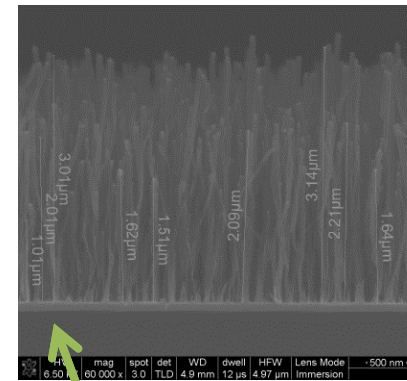
45 mm from center



Center of wafer



20 mm from center



40 mm from center

Center:
1.6-3.2
μm

+10mm
(From center):
1.6-3.1 μm

+20mm:
1.6-3.2
μm

+30mm:
1.4-3.1
μm

+40mm:
1.6-3.1
μm

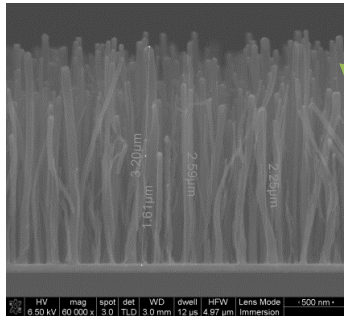
+45mm:
1.3-2.5
μm

Length of the CNTs are in the ranges written above (μm)

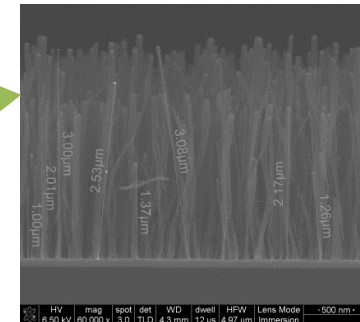
Process parameters Recipe: PECVD NH3.txt ; **Growth time:** 10 min

Gasses growth: N2:100 sccm NH3:160 C2H2:40; **Substrate:** Si/TiW/Ni (100 nm TiW/7 nm Ni)

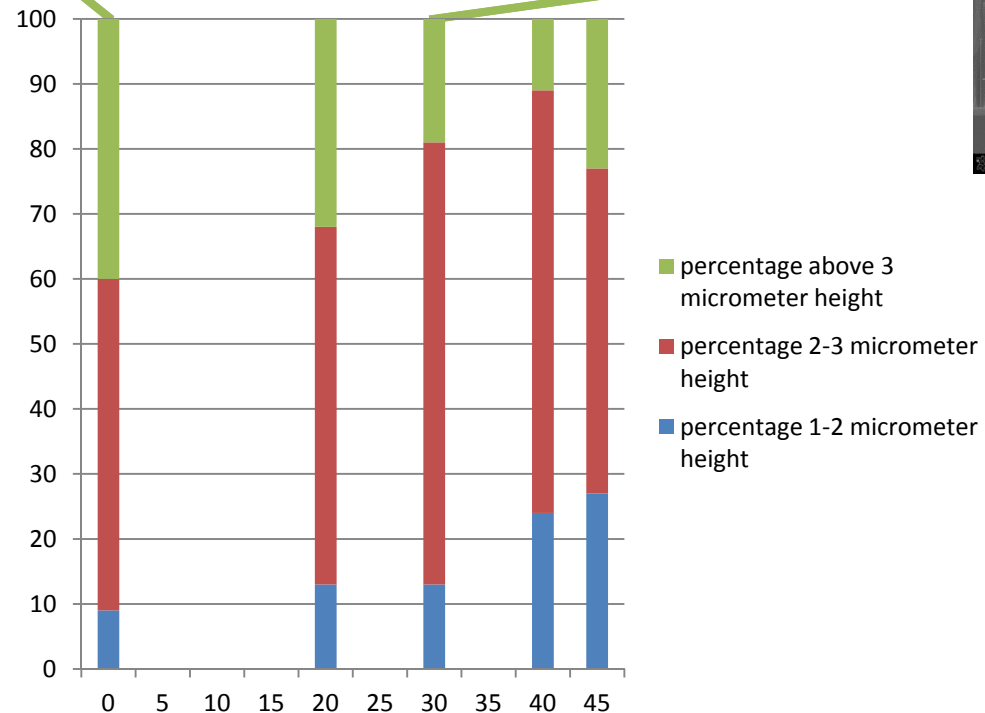
Length distribution of CNTs



Center of wafer



30 mm from center



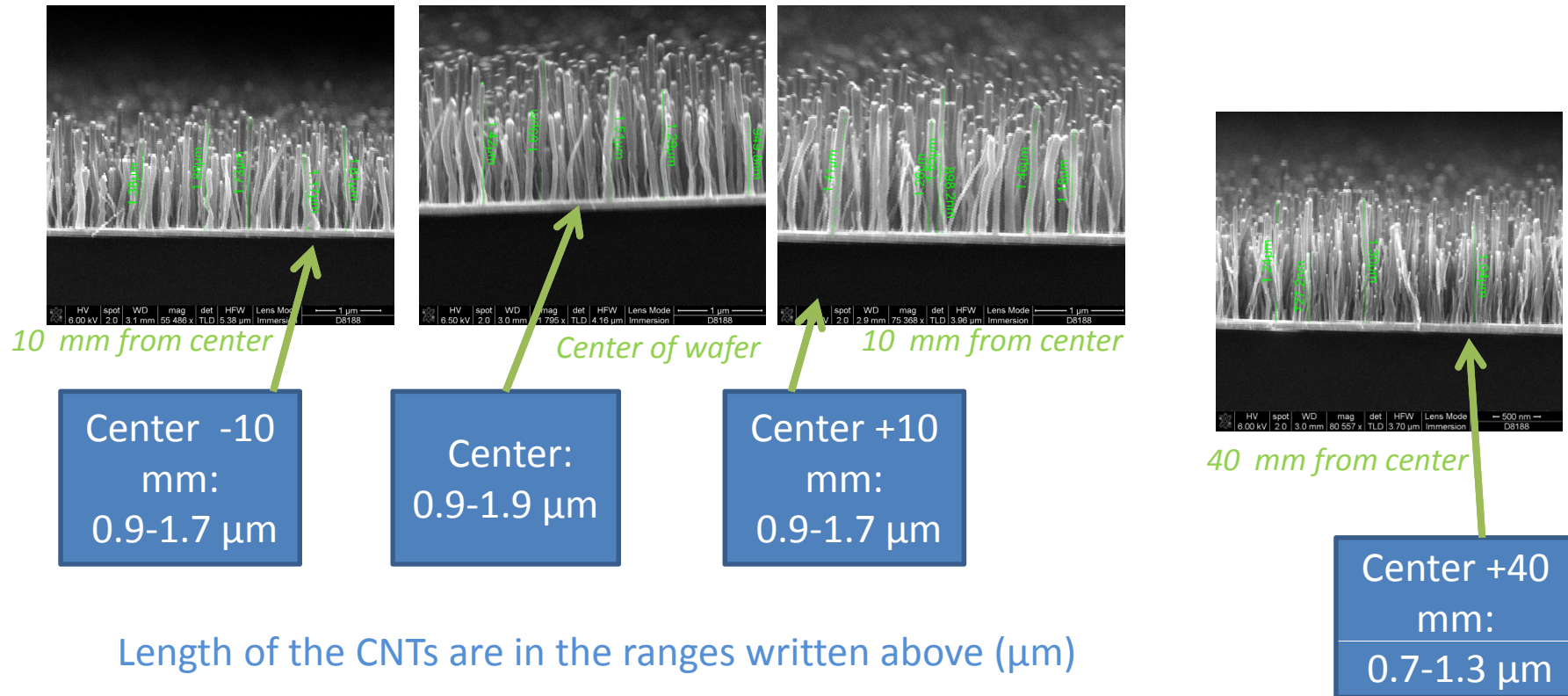
Note: only checked one image from each place on the wafer

0 mm,
center

45mm,
from center of the wafer

Length of CNTs on one wafer: 4 measurement points on the wafer

Another wafer



Process parameters Recipe: PECVD NH3.txt ; Growth time: 5 min

Gasses growth: N2:100 sccm NH3:160 C2H2:40; **Substrate:** Si/TiW/Ni (100 nm TiW/7 nm Ni)

(Wafer 5)